INTERSIL

2N2607-2N2609
2N2609 JAN
P-Channel JFET

1

APPLICATIONS

- Low-level Choppers
- Data Switches
- Commutators

ABSOLUTE MAXIMUM RATINGS

@ 25°C (unless otherwise noted)

Maximum Temperatures

Storage Temperature	-65°C to +200°C
Operating Junction Temperature	+175°C
Lead Temperature (Soldering, 10 sec.)	+260°C

Maximum Power Dissipation

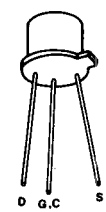
Device Dissipation @ Free Air Temperature	300 mW
Linear Derating	2.0 mW/°C

Maximum Voltages & Current

V_{DG}	Drain to Gate Voltage	30 V
V_{SG}	Source to Gate Voltage	30 V
I_G	Gate Current	50 mA

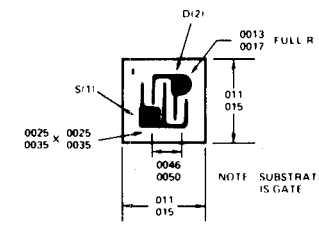
PIN CONFIGURATION

TO-18

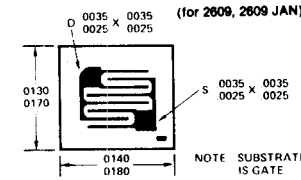


CHIP TOPOGRAPHY

5010 (for 2N2607, 8)



5503B (for 2609, 2609 JAN)



ORDERING INFORMATION

TO-18	WAFER	DICE
2N2607	2N2607/W	2N2607/D
2N2608	2N2608/W	2N2608/D
2N2609	2N2609/W	2N2609/D
2N2609 JAN	2N2609 JAN/W	2N2609 JAN/D

ELECTRICAL CHARACTERISTICS (@ 25°C unless otherwise noted)

Characteristic		Test Conditions		2N2607		2N2608		2N2609		Unit
				Min	Max	Min	Max	Min	Max	
I_{GSS}	Gate-Source Cutoff Current	V_{GS} = 30 V, V_{DS} = 0			3		10		30	nA
		V_{GS} = 5 V, V_{DS} = 0, T_A = 150° C			3		10		30	μA
BV_{GDS}	Gate-Drain Breakdown Voltage	I_G = 1 μA, V_{DS} = 0		30		30		30		V
V_P	Gate-Source Pinch-Off Voltage	V_{DS} = -5 V, I_D = -1 μA		1	4	1	4	1	4	V
I_{DSS}	Drain Current at Zero Gate Voltage	V_{DS} = -5 V, V_{GS} = 0		-0.30	-1.50	-0.90	-4.50	-2	-10	mA
g_{fs}	Small-Signal Common-Source Forward Transconductance	V_{DS} = -5 V, V_{GS} = 0, f = 1 kHz		330		1000		2500		μmho
C_{iss}	Gate-Source Input Capacitance	V_{DS} = -5 V, V_{GS} = 1 V, f = 140 kHz			10		17		30	pF
NF	Noise Figure	V_{DS} = -5 V, V_{GS} = 0, f = 1 kHz	R_G = 10 MΩ		3					dB
			R_G = 1 MΩ				3		3	